Preferred Device

Silicon Controlled Rectifiers

Reverse Blocking Thyristors

Designed primarily for half-wave ac control applications, such as motor controls, heating controls and power supply crowbar circuits.

- Glass Passivated Junctions with Center Gate Fire for Greater Parameter Uniformity and Stability
- Small, Rugged, Thermowatt Constructed for Low Thermal Resistance, High Heat Dissipation and Durability
- Blocking Voltage to 800 Volts
- 300 A Surge Current Capability
- Insulated Package Simplifies Mounting
- **%** Indicates UL Registered File #E69369
- Device Marking: Logo, Device Type, e.g., MCR225-8FP, Date Code

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Peak Repetitive Off-State Voltage ⁽¹⁾ (T _J = -40 to +125°C, Sine Wave, 50 to 60 Hz, Gate Open) MCR225-8FP MCR225-10FP	V _{DRM} , VRRM	600 800	Volts
On-State RMS Current (T _C = +70°C) (180° Conduction Angles)	I _{T(RMS)}	25	Amps
Peak Non-repetitive Surge Current (1/2 Cycle, Sine Wave 60 Hz, T _C = +70°C)	I _{TSM}	300	Amps
Circuit Fusing (t = 8.3 ms)	l ² t	375	A ² s
Forward Peak Gate Power ($T_C = +70^{\circ}C$, Pulse Width $\leq 1.0 \mu s$)	P _{GM}	20	Watts
Forward Average Gate Power (T _C = +70°C, t = 8.3 ms)	P _{G(AV)}	0.5	Watt
Forward Peak Gate Current ($T_C = +70^{\circ}C$, Pulse Width $\leq 1.0 \mu s$)	I _{GM}	2.0	Amps
RMS Isolation Voltage (T _A = 25°C, Relative Humidity ≤ 20%) (%)	V _(ISO)	1500	Volts
Operating Junction Temperature Range	TJ	–40 to +125	ç
Storage Temperature Range	T _{stg}	-40 to +150	ç

⁽¹⁾ V_{DRM} and V_{RRM} for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; however, positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.



ON Semiconductor

http://onsemi.com

ISOLATED SCRs (%) 25 AMPERES RMS 600 thru 800 VOLTS





ISOLATED TO-220 Full Pack CASE 221C STYLE 2

PIN ASSIGNMENT				
1	Cathode			
2	Anode			
3	Gate			

ORDERING INFORMATION

Device	Package	Shipping	
MCR225-8FP	ISOLATED TO220FP	500/Box	
MCR225-10FP	ISOLATED TO220FP	500/Box	

Preferred devices are recommended choices for future use and best overall value.

THERMAL CHARACTERISTICS

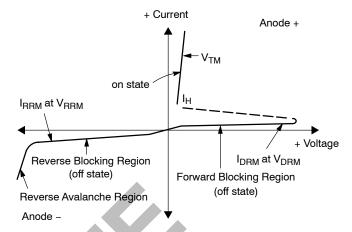
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{ heta JC}$	1.5	°C/W
Thermal Resistance, Case to Sink	R _{0CS}	2.2 (typ)	°C/W
Thermal Resistance, Junction to Ambient	$R_{ heta JA}$	60	°C/W
Maximum Lead Temperature for Soldering Purposes 1/8" from Case for 10 Seconds	TL	260	°C

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS		1	·	·	L
Peak Repetitive Forward or Reverse Blocking Current $(V_D = \text{Rated V}_{DRM}, V_{RRM}; \text{Gate Open}) \qquad \qquad T_J = 25^{\circ}\text{C} \\ T_J = 125^{\circ}\text{C}$	I _{DRM} , I _{RRM}	_	_	10 2	μA mA
ON CHARACTERISTICS					
Peak Forward On-State Voltage ⁽¹⁾ (I _{TM} = 50 A)	V _{TM}		_	1.8	Volts
Gate Trigger Current (Continuous dc) (V _{AK} = 12 Vdc, R _L = 100 Ohms)	I _{GT}	_	70	40	mA
Gate Trigger Voltage (Continuous dc) (V _{AK} = 12 Vdc, R _L = 100 Ohms)	V _{GT}	% -3	0.8	1.5	Volts
Gate Non-Trigger Voltage (V _{AK} = 12 Vdc, R _L = 100 Ohms, T _J = 125°C)	V _{GD}	0.2		_	Volts
Holding Current (V _{AK} = 12 Vdc, Initiating Current = 200 mA, Gate Open)	CSIH (I)	<u>Gl</u>	20	40	mA
Turn-On Time (I _{TM} = 25 A, I _{GT} = 40 mAdc)	t _{gt}	KO.	1.5	_	μs
Turn-Off Time (V _{DRM} = Rated Voltage) (I _{TM} = 25 A, I _R = 25 A) (I _{TM} = 25 A, I _R = 25 A, T _J = 125°C)	UP OR	_	15 35	_	μs
DYNAMIC CHARACTERISTICS					
Critical Rate-of-Rise of Off-State Voltage (Gate Open, V _D = Rated V _{DRM} , Exponential Waveform)	dv/dt	_	100	_	V/μs
(Gate Open, V _D = Rated V _{DRM} , Exponential Waveform) 1) Pulse Test: Pulse Width = 1.0 ms, Duty Cycle ≤ 2%.					

⁽¹⁾ Pulse Test: Pulse Width = 1.0 ms, Duty Cycle ≤ 2%

Voltage Current Characteristic of SCR

Symbol	Parameter
V_{DRM}	Peak Repetitive Off State Forward Voltage
I _{DRM}	Peak Forward Blocking Current
V_{RRM}	Peak Repetitive Off State Reverse Voltage
I _{RRM}	Peak Reverse Blocking Current
V_{TM}	Peak on State Voltage
I _H	Holding Current



TYPICAL CHARACTERISTICS

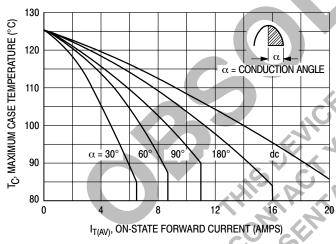


Figure 1. Average Current Derating

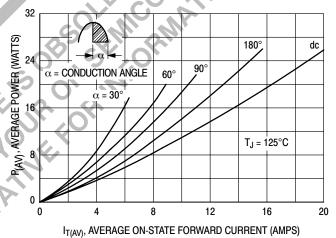
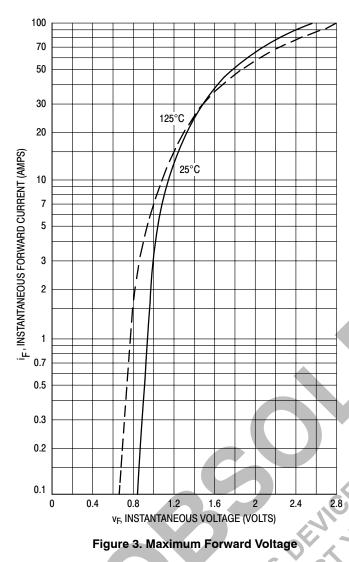


Figure 2. Maximum On-State Power Dissipation



 $T_C = 85^{\circ}C$ f = 60 Hz SURGE IS PRÉCÉDED AND FOLLOWED BY RATED CURRENT 8 10 NUMBER OF CYCLES

Figure 4. Maximum Non-Repetitive Surge Current

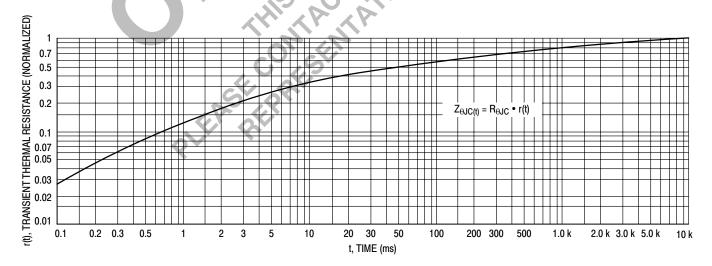
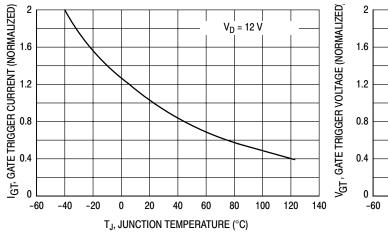


Figure 5. Thermal Response



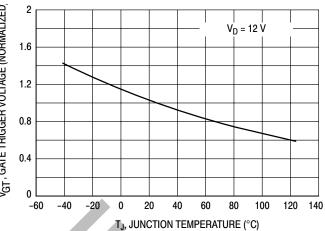
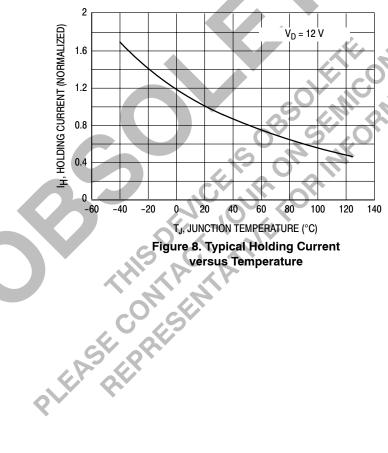


Figure 6. Typical Gate Trigger Current versus Temperature

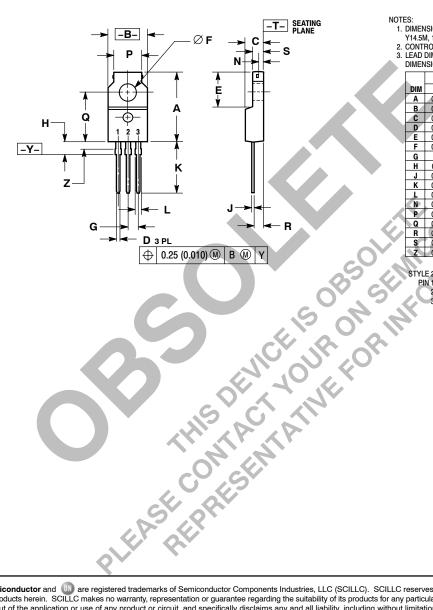
Figure 7. Typical Gate Trigger Voltage versus Temperature



PACKAGE DIMENSIONS

ISOLATED TO-220 Full Pack

CASE 221C-02 ISSUE C



NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: INCH.
 LEAD DIMENSIONS UNCONTROLLED WITHIN DIMENSION Z.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
Α	0.680	0.700	17.28	17.78
В	0.388	0.408	9.86	10.36
C	0.175	0.195	4.45	4.95
D	0.025	0.040	0.64	1.01
E	0.340	0.355	8.64	9.01
F	0.140	0.150	3.56	3.81
G	0.100	100 BSC 2.5		BSC
Н	0.110	0.155	2.80	3.93
J	0.018	0.028	0.46	0.71
K	0.500	0.550	12.70	13.97
T	0.045	0.070	1.15	1.77
N	0.049	4	1.25	
P	0.270	0.290	6.86	7.36
Q	0.480	0.500	12.20	12.70
R	0.090	0.120	2.29	3.04
S 7	0.105	0.115	2.67	2.92
7	0.070	0.090	1 78	2 28

PIN 1. CATHODE 2. ANODE 3. GATF

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